



08/462742

#4 Preliminary

Docket: 0756-1299

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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Divisional PATENT application of )  
Hongyong ZHANG et al. )  
Based on Serial No. 08/248,220 ) Art Unit: 2508  
Filed: June 5, 1995 ) Examiner: S. Loke  
For: SEMICONDUCTOR DEVICE AND )  
FABRICATION METHOD OF THE )  
SAME ) June 5, 1995

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents and Trademarks  
Washington, D.C. 20231

Sir:

Please preliminarily amend the subject application as follows:

IN THE CLAIMS

Add new claims 14-25 as follows:

Sub-  
C2  
--14. A method for fabricating a semiconductor device, comprising the steps of:

forming a silicon film having an amorphous on a substrate;  
preparing a metal element which promotes crystallization before  
or after formation of the silicon film, to introduce the metal element into an  
introducing region of the silicon film; and  
crystallizing the silicon film,  
wherein the silicon film is crystal-grown from the introducing